TOSHIBA CCD Linear Image Sensor CCD (Charge Coupled Device)

TCD1711DG



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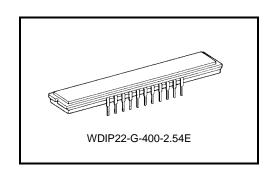
TCD1711DG

The TCD1711DG is a high sensitive and low dark current 7450 elements CCD linear image sensor.

The device contains a row of 7450 elements photodiodes which provide 24 lines/mm across a A3 size paper. The device is operated by 5.0 V pulse and 10 V power supply.

Features

- Number of Image Sensing Elements: 7450 elements
- Image Sensing Element Size: 4.7 μm by 4.7 μm on 4.7 μm center
- Photo Sensing Region: High sensitive PN photodiode
- Clock: 2-phase (5 V)
- Power Supply Voltage: 10 V (typ.)
 Internal Circuit: Clamp circuit
 Package: 22 pin CERDIP



ABSOLUTE MAXIMUM RATINGS (Note 1)

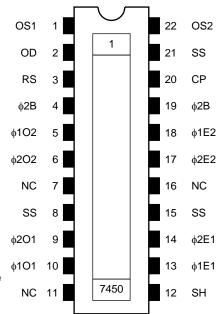
Characteristics	Symbol	Rating	Unit	
Clock pulse voltage	V_{ϕ}		V	
Shift pulse voltage	VsH	-0.3 to +8.0		
Reset pulse voltage	V _{RS}	-0.3 10 +0.0		
Clamp pulse voltage	VCP			
Power supply voltage	V _{OD}	-0.3 to +15.0		
Operating temperature	T _{opr}	0 to 60	°C	
Storage temperature	T _{stg}	-25 to +85	°C	

Note 1: All voltages are with respect to SS terminals (ground).

None of the ABSOLUTE MAXIMUM RATINGS must be exceeded, even instantaneously.

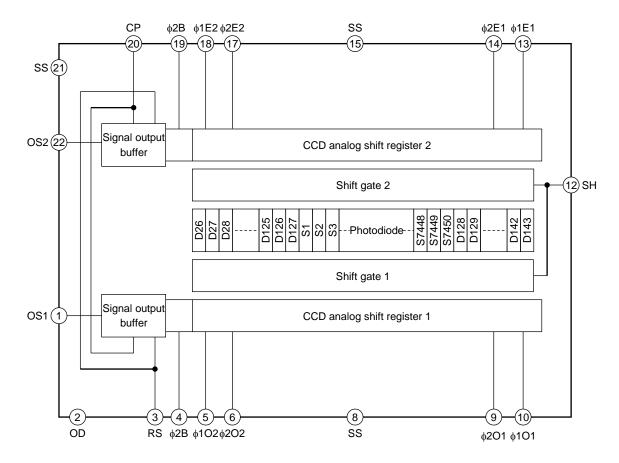
If any one of the ABSOLUTE MAXIMUM RATINGS is exceeded, the electrical characteristics, reliability and life time of the device cannot be guaranteed. If the ABSOLUTE MAXIMUM RATINGS are exceeded, the device can be permanently damaged or degraded. Create a system design in such a manner that any of the ABSOLUTE MAXIMUM RATINGS will not be exceeded under any circumstances.

Pin Connections (top view)





Circuit Diagram



Pin Names

Pin No.	Symbol	Name	Pin No.	Symbol	Name
1	OS1	Output signal 1	22	OS2	Output signal 2
2	OD	Power supply	21	SS	Ground
3	RS	Reset gate	20	СР	Clamp gate
4	ф2В	Last stage transfer clock (phase 2)	19	ф2В	Last stage transfer clock (phase 2)
5	φ1Ο2	Transfer clock 2 (phase 1)	18	φ1E2	Transfer clock 2 (phase 1)
6	ф2О2	Transfer clock 2 (phase 2)	17	φ2E2	Transfer clock 2 (phase 2)
7	NC	Non connection	16	NC	Non connection
8	SS	Ground	15	SS	Ground
9	ф2О1	Transfer clock 1 (phase 2)	14	φ2E1	Transfer clock 1 (phase 2)
10	φ1Ο1	Transfer clock 1 (phase 1)	13	φ1E1	Transfer clock 1 (phase 1)
11	NC	Non connection	12	SH	Shift gate

2



Optical/Electrical Characteristics

Ta = 25°C, VoD = 10 V, $V_{\phi} = VSH = VRS = VCP = 5$ V (pulse), $f_{\phi} = 1.0$ MHz, tint (integration time) = 10 ms, light source = daylight fluorescent lamp

Characteristics	Symbol	Min	Тур.	Max	Unit	Note	
Sensitivity	R	12	15	18	V/Ix·s	_	
Dh. da a sa	PRNU	_	4	10	%	(Note 2)	
Photo response non uniformity	PRNU (3)	_	6	12	mV	(Note 8)	
Saturation output voltage	VSAT	1.5	1.8	_	V	(Note 3)	
Saturation exposure	SE	0.08	0.12	_	lx⋅s	(Note 4)	
Dark signal voltage	Vdrk	_	1	3	mV	(Note 5)	
Dark signal non uniformity	DSNU	_	4	10	mV	(Note 5)	
DC power dissipation	PD	_	250	375	mW	_	
Total transfer efficiency	TTE	92	98	_	%	_	
Output impedance	ZO	_	0.2	1.0	kΩ	_	
Dynamic range	DR	_	1800	_	_	(Note 6)	
DC output signal voltage	Vos1	3.0	4.5	6.0	V	(NI=1= =)	
	V _{OS2}	3.0	4.5	6.0	V	(Note 7)	
DC differential error voltage	V _{OS1} - V _{OS2}	_	_	300	mV	_	
Random noise	N _{Dσ}	_	1.0	_	mV	(Note 9)	

Note 2: PRNU is defined on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature, where measured approximately 750 mV of signal output.

$$PRNU = \frac{\Delta X}{\overline{X}} \times 100 \text{ (\%)}$$

Where \overline{X} is average of total signal output and ΔX is the maximum deviation from \overline{X} under uniform illumination. (OS1)

In the case of 3725 elements (OS2), the condition is the same as above too.

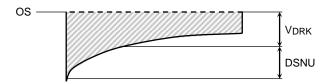
Note 3: VSAT is defined as the minimum saturation output voltage of all effective pixels.

Note 4: Definition of SE:

$$SE = \frac{VSAT}{R}$$

Note 5: VDRK is defined as average dark signal voltage of all effective pixels.

DSNU is defined by the difference between average value (VDRK) and the maximum value of the dark voltage.



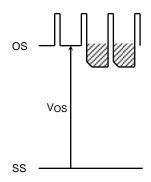
Note 6: Definition of DR:

$$DR = \frac{VSAT}{VDRK}$$

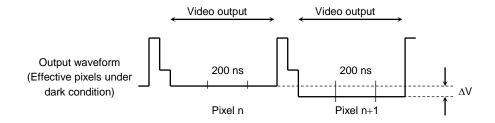
 $\label{local_vdr} \textit{VDRK} \ is \ proportional \ to \ tint \ (integration \ time). \ So \ shorter \ integration \ time \ makes \ wider \ dynamic \ range.$



Note 7: DC output signal voltage is defined as follows.



- Note 8: PRNU (3) is defined as the maximum voltage with next pixel, where measured approximately 50 mV of signal output.
- Note 9: Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.



- 1) Two adjacent pixels (pixel n and n+1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output periods averaged over 200 ns period to get V(n) and V(n+1).
- 3) V(n+1) is subtracted from V(n) to get ΔV .

$$\Delta V = V(n) - V(n+1)$$

4) The standard deviation of ΔV is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} \!\! \left| \Delta V_i \right| \qquad \qquad \sigma = \sqrt{\frac{1}{30} \sum_{i=1}^{30} \!\! \left(\!\! \left| \Delta V_i \right| - \overline{\Delta V} \right)^2}$$

- 5) Procedure 2), 3) and 4) are repeated 10 times to get sigma value.
- 6) 10 sigma values are averaged.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

7) $\bar{\sigma}$ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as follows.

$$ND\sigma = \frac{1}{\sqrt{2}}\overline{\sigma}$$



Recommended Operating Conditions ($Ta = 25^{\circ}C$)

For best performance, the device should be used within the Recommended Operating Conditions.

Characteristics		Symbol	Min	Тур.	Max	Unit
Clock pulse voltage	"H" level	V _φ 1Ε, V _φ 1Ο V _φ 2Ε, V _φ 2Ο	4.5	5.0	5.5	V
	"L" level		0	0	0.5	
Last stage clock pulse	"H" level	Vion	4.5	5.0	5.5	V
voltage	"L" level	V _ф 2B	0	0	0.5	
Shift pulse voltage	"H" level	VsH	4.5	5.0	5.5	V
	"L" level		0	0	0.5	
Reset pulse voltage	"H" level	VRS	4.5	5.0	5.5	V
	"L" level		0	0	0.5	
Clamp pulse voltage	"H" level	\/	4.5	5.0	5.5	
	"L" level	VCP	0	0	0.5	v
Power supply voltage		V _{OD}	9.5	10.0	11.0	V

Clock Characteristics (Ta = 25°C)

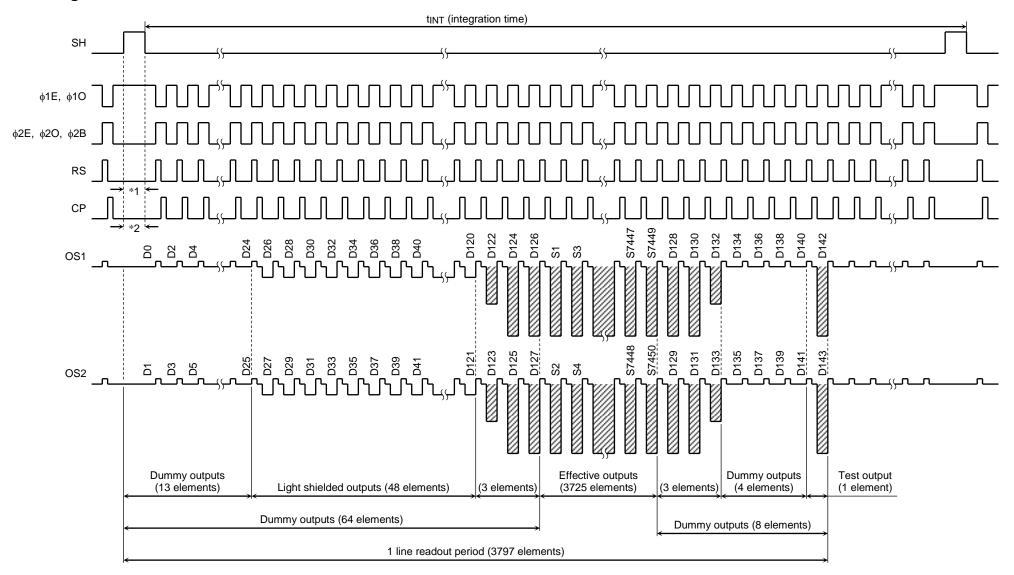
For best performance, the device should be used within the Recommended Operating Conditions.

Characteristics	Symbol	Min	Тур.	Max	Unit	
Clock pulse frequency	fφ	_	1	30	MHz	
Reset pulse frequency	f _{RS}	_	1	30	MHz	
Clamp pulse frequency	fCP	_	1	30	MHz	
Clash appairance (Nata 40)	СфЕ	_	70	_	ي ر	
Clock capacitance (Note 10)	C_{\phiO}	_	70	_	pF	
Last stage clock capacitance	СфВ	_	10	_	pF	
Shift gate capacitance	CsH	_	20	_	pF	
Reset gate capacitance	CRS	_	10	_	pF	
Clamp gate capacitance	ССР	_	10	_	pF	

Note 10: VOD = 10 V, Input capacitance per a pin.

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Timing Chart



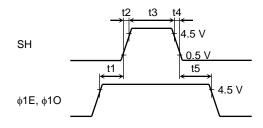
^{*1:} Keep the RS pin "L" level.

^{*2:} Keep the CP pin "L" level.

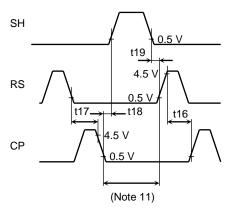


Timing Requirements

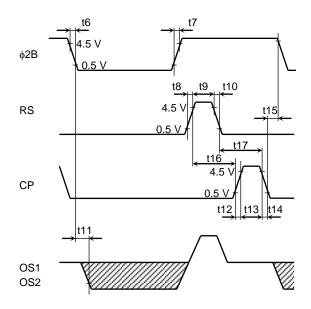




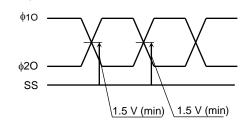
SH, RS, CP timing

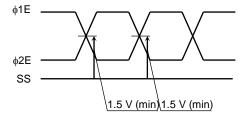


 $\phi 2$, RS, CP, OS timing



φ1, φ2 cross point





Note 11: Keep the RS and CP pins "L" level.

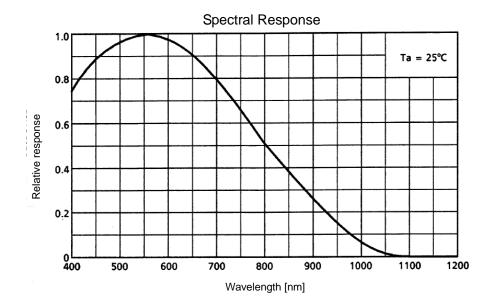


Characteristics	Symbol	Min	Typ. (Note 12)	Max	Unit
Pulse timing of SH and φ1E, φ1O	t1, t5	200	500	_	ns
SH pulse rise time, fall time	t2, t4	0	50	_	ns
SH pulse width	t3	1000	1500	_	ns
φ2B pulse rise time, fall time	t6, t7	0	100	_	ns
RS pulse rise time, fall time	t8, t10	0	20	_	ns
RS pulse width	t9	8	100	_	ns
Video data delay time	t11	_	8	_	ns
CP pulse rise time, fall time	t12, t14	0	20	_	ns
CP pulse width	t13	8	100	_	ns
Pulse timing of ϕ 2B and CP	t15	0	50	_	ns
Pulse timing of RS and CP	t16	0	100	_	ns
	t17	8	100	_	ns
Pulse timing of SH and CP	t18	200	_	_	ns
Pulse timing of SH and RS	t19	200	_	_	ns

Note 12: Measured with fRS = 1 MHz.



Typical Spectral Response





Cautions

1. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

CCD Image Sensor is protected against static electricity, but inferior puncture mode device due to static electricity is sometimes detected. In handing the device, it is necessary to execute the following static electricity preventive measures, in order to prevent the trouble rate increase of the manufacturing system due to static electricity.

- a. Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.
- Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.
- c. Ground the tools such as soldering iron, radio cutting pliers of or pincer.
- d. Ionized air is recommended for discharge when handling CCD image sensors.

It is not necessarily required to execute all precaution items for static electricity.

It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

2. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Mounting on a PCB

This package is sensitive to mechanical stress.

TOSHIBA recommends using IC inserters for mounting, instead of using lead forming equipment. Since this package is not strong against mechanical stress, you should not reform the lead frame. We recommend to use an IC-inserter when you assemble to PCB.

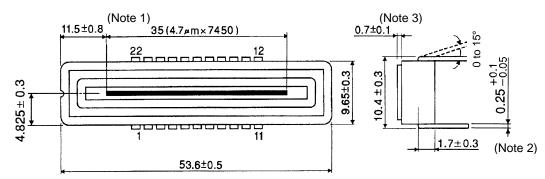
5. Soldering

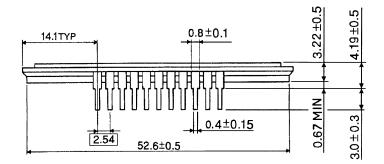
Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

Using a soldering iron, complete soldering within three seconds for lead temperatures of up to 350°C.



Package Dimensions





Note 1: Distance between the edge of the package and the first pixel (S1)

Note 2: Distance between the top of chip and bottom of the package

Note 3: Glass thickness (n = 1.5)



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